

ETCHING METHOD AND PLASMA PROCESSING APPARATUS

ABSTRACT

5 An etching method according to an example embodiment includes (a) supplying a film forming gas into a chamber through a gas feeding port of a showerhead containing silicon to form a protective film on an inner wall of the gas feeding port; and (b) supplying an etching gas into the chamber through the gas feeding port on which the protective film is formed to etch a substrate in the chamber with plasma generated from the etching gas.

Fig. 3